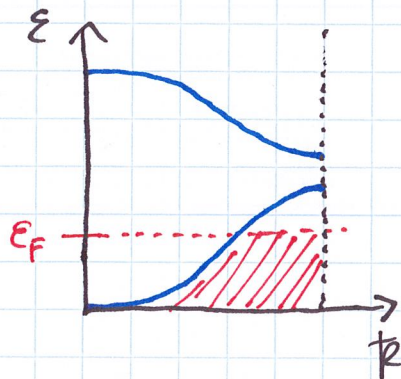


## Semi-classical Model: Summary

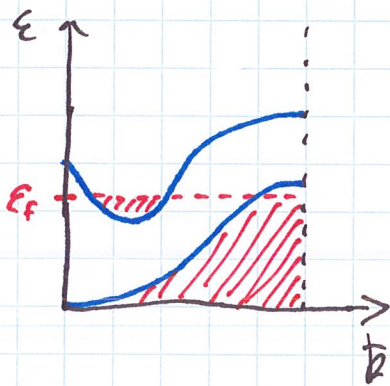
- quantum particles ( $\bar{e}$ ) in a periodic crystal potential
- Bloch Theory
- periodic potential separates Free  $\bar{e}$  energies into bands.  $\Rightarrow$  Band gap
- Each band contains  $N$   $k$ -states ( $2N$   $\bar{e}$  states)

### Material Types



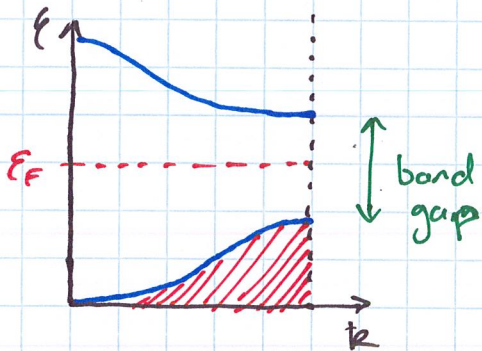
Metal  $\rightarrow$  Fermi energy lies in a band

e.g. Na, Cu, Ag, Au ... a lot



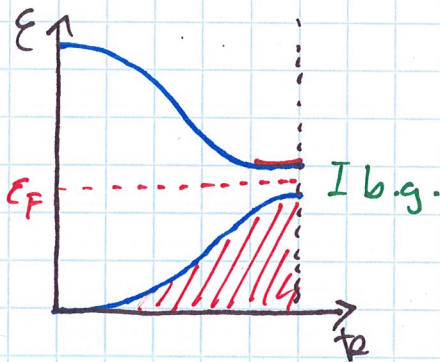
Semi-metal  $\rightarrow$   $E_F$  lies in two overlapping bands

e.g. Ca



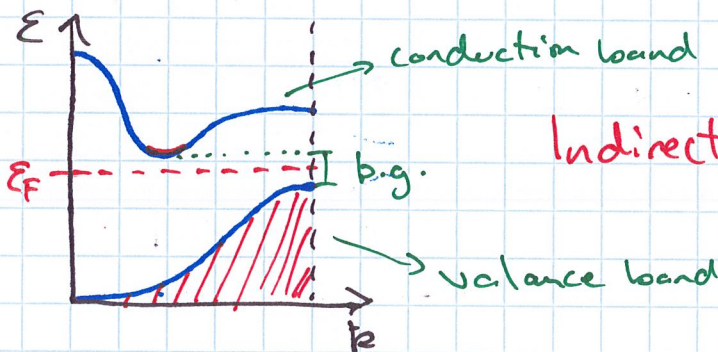
Insulator  $\rightarrow E_F$  lies between two bands i.e. in the band-gap  
 $\rightarrow$  large band gap.

e.g. C



Direct bandgap e.g. GaAs

Semiconductor  $\rightarrow E_F$  lies in bandgap  
 $\rightarrow$  small band gap.



Indirect bandgap. e.g. Si

$\rightarrow$  Conductivity requires higher-energy states (add energy to  $e^-$ 's)

$\rightarrow$  if none are available  $\rightarrow$  can not conduct.

$\rightarrow$  since each band can hold  $2N$   $e^-$ , an even # of  $E$  atoms is required for an insulator

## Conductivity:

$$\text{recall} \rightarrow \vec{v}_n(\vec{k}) = \frac{1}{\hbar} \nabla_{\vec{k}} \mathcal{E}(\vec{k})$$

Recall: current density  $\vec{j} = -e\vec{v}$

$$\begin{aligned} \vec{j} &= -e \sum_{\vec{k}} \vec{v}_{\vec{k}} \\ &= -\frac{e}{\hbar} \int \frac{1}{4\pi^3} \nabla_{\vec{k}} \mathcal{E}_{\vec{k}} d\vec{k} \end{aligned}$$

→ for a filled band,  $\mathcal{E}_{\vec{k}}$  is periodic, integral over all  $\vec{k}$  yields  $= 0$ . App. I for \* proof.

→ only  $\bar{e}$  in partially filled bands contribute to conductivity → electrical &  $\bar{e}$  part of thermal

→ Filled bands are inert

→ partially filled band:

$$\vec{j} = \frac{-e}{4\pi^3} \int_{\text{occupied}} \vec{v}(\vec{k}) d\vec{k}$$

\* → generally: integral over complete Brillouin zone of the gradient of a periodic function is 0.

## Holes:

$$\rightarrow j = \frac{-e}{4\pi^3} \int_{\text{occupied}} \bar{v}_k dk$$

Filled band:  $j = 0$

$$0 = \int_{\text{zone}} v_k dk = \int_{\text{occ.}} v_k dk + \int_{\text{unocc.}} v_k dk$$

$A_p$

$$\therefore j = \frac{-e}{4\pi^3} \int_{\text{occ.}} v_k dk = \frac{+e}{4\pi^3} \int_{\text{unocc.}} v_k dk$$

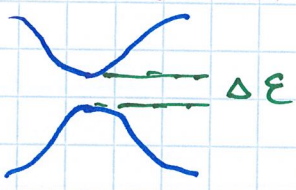
- > current carried by (-) charge carriers occupying "filled" states equivalent to (+) charge carriers occupying "unfilled" states.
- > hole = absence of  $e^-$  (& vice versa)
- > holes, (+) charge carriers, critical to semi-conductor physics => doping.
- > holes &  $e^-$  can interact & bind => exciton

## Semi-conductors

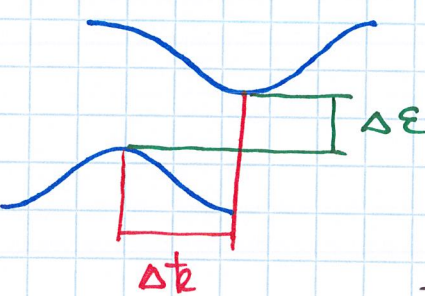
→ require heat or optical energy (i.e. photon) to promote  $\bar{e}$  into conduction band.

⇒ photovoltaics

Direct band gap: only a photon is req'd to move from valance to conduction band.  
i.e. transition → absorb/emit photon.  
 $\Delta E$



Indirect band gap: transition also requires a momentum transfer,  $\Delta k$  and  $\Delta E$   
→ since photons carry almost no momentum... phonons are req'd. (lattice vibrations).  
→ reduced efficiency.



## Final Notes:

- 1)  $\bar{p} \neq \hbar \mathbf{k}$  ⇒ momentum is not just  $\hbar \mathbf{k}$  but is still related to  $\mathbf{k}$ . ⇒  $\bar{p} = m \mathbf{v}_{\mathbf{k}} = \frac{m}{\hbar} \nabla_{\mathbf{k}} \epsilon_{\mathbf{k}}$
- 2) Insulator requires even # of  $\bar{e}$  / atom  
↳ otherwise  $\epsilon_F$  guaranteed to lie in band. (2N  $\bar{e}$  per band).
- 3) Still nothing about  $\mathcal{Z}$ : Bloch's Theory accounts for interaction of  $\bar{e}$  w/ stationary lattice  
→ need dynamic lattice (phonons) to account for scattering!